Hsien-Wen Wan

List of Publications by Year
in descending order

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22 papers	96 citations	1684188 5 h-index	1474206 9 g-index
22 all docs	22 docs citations	22 times ranked	75 citing authors

#	Article	IF	Citations
1	Attainment of low subthreshold slope in planar inversion-channel InGaAs MOSFET with in situ deposited Al₂O₃/Y₂O₃ as a gate dielectric. Japanese Journal of Applied Physics, 2022, 61, SC1018.	1.5	4
2	Low thermal budget epitaxial lift off (ELO) for Ge (111)-on-insulator structure. Japanese Journal of Applied Physics, 2022, 61, SC1024.	1.5	1
3	In-situ deposited HfO₂ and Y₂O₃ on epi-Si/p-Geâ€"a comparative study of the interfacial properties and reliability. Japanese Journal of Applied Physics, 2022, 61, SC1074.	1.5	2
4	A Synchrotron Radiation Photoemission Study of SiGe(001)-2Ã—1 Grown on Ge and Si Substrates: The Surface Electronic Structure for Various Ge Concentrations. Nanomaterials, 2022, 12, 1309.	4.1	2
5	High-Ge-Content Si_{1â€"x}Ge_x Gate Stacks with Low-Temperature Deposited Ultrathin Epitaxial Si: Growth, Structures, Low Interfacial Traps, and Reliability. ACS Applied Electronic Materials, 2022, 4, 2641-2647.	4.3	1
6	(Invited) Thin Epitaxial Single-Crystal Si on Sige Followed By in-Situ Deposition of High-k Dielectrics â€" Novel Gate Stacks for Achieving Extremely Low D_{it} and Highly Reliable SiGe MOS. ECS Meeting Abstracts, 2022, MA2022-01, 1067-1067.	0.0	0
7	Microscopic Views of Ge Segregation and Scavenging Ge on Thin Si on Epi-Ge(001). ECS Meeting Abstracts, 2022, MA2022-01, 1053-1053.	0.0	0
8	Low-Temperature-Grown Single-Crystal Si Epitaxially on Ge, Followed by Direct Deposition of High-Îº Dielectricsâ€"Attainment of Low Interfacial Traps and Highly Reliable Ge MOS. ACS Applied Electronic Materials, 2021, 3, 2164-2169.	4.3	8
9	In situ Y2O3 on p-In0.53Ga0.47Asâ€"Attainment of low interfacial trap density and thermal stability at high temperatures. Applied Physics Letters, 2021, 118, .	3.3	6
10	Oxidation and hydrogenation of SiGe(0 0 1)-2ÂÃ—Â1 at room temperature and in situ annealing: A synchrotron radiation photoemission study. Applied Surface Science, 2021, 569, 150962.	6.1	0
11	Low-temperature grown single-crystal Si on epi Ge(001)-2 Ã— 1 and its oxidation: electronic structure study via synchrotron radiation photoemission. Applied Physics Express, 2020, 13, 085504.	2.4	7
12	Surface electronic structure of Si_{1â^'x}Ge _x (001)-2 Ã— 1: a synchrotron radiation photoemission study. Applied Physics Express, 2020, 13, 095503.	2.4	6
13	Fundamental Understanding of Oxide Defects in HfO2 and Y2O3 on GaAs(001) with High Thermal Stability. , 2019, , .		1
14	BTI Characterization of MBE Si-Capped Ge Gate Stack and Defect Reduction via Forming Gas Annealing. , 2019, , .		3
15	Microscopic Views of Atomic and Molecular Oxygen Bonding with epi Ge(001)-2 Ã— 1 Studied by High-Resolution Synchrotron Radiation Photoemission. Nanomaterials, 2019, 9, 554.	4.1	5
16	Epitaxy of High-Quality Single-Crystal Hexagonal Perovskite YAlO₃ on GaAs(111)A Using Laminated Atomic Layer Deposition. Crystal Growth and Design, 2019, 19, 2030-2036.	3.0	3
17	Atomic Nature of the Growth Mechanism of Atomic Layer Deposited High-Îº Y₂O₃ on GaAs(001)-4 Ã— 6 Based on in Situ Synchrotron Radiation Photoelectron Spectroscopy. ACS Omega, 2018, 3, 2111-2118.	3.5	8
18	Exciton Localization of High-Quality ZnO/Mg_xZn_{1â€"x}O Multiple Quantum Wells on Si (111) with a Y₂O₃ Buffer Layer. ACS Applied Nano Materials, 2018, 1, 3829-3836.	5.0	5

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19	Atomic layer deposited single-crystal hexagonal perovskite YAlO3 epitaxially on GaAs(111)A. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, 01B123.	2.1	2
20	Perfecting the Al2O3/In0.53Ga0.47As interfacial electronic structure in pushing metal-oxide-semiconductor field-effect-transistor device limits using in-situ atomic-layer-deposition. Applied Physics Letters, 2017, 111, .	3.3	15
21	Surface electronic structure of epi germanium (001)-2 Ã— 1. Applied Physics Express, 2017, 10, 075701.	2.4	16
22	Scavenging Segregated Ge on Thin Single-Crystal Si Epitaxially Grown on Ge. ACS Applied Electronic Materials, 0, , .	4.3	1